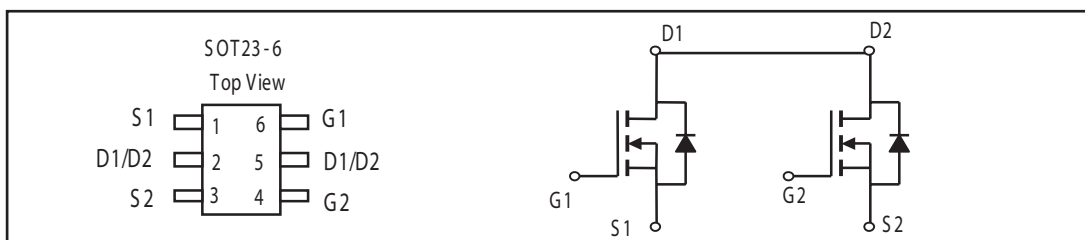


## Dual N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V <sub>DS</sub>	I <sub>D</sub>	R <sub>DS(ON)</sub> (m ohm)Max
20V	5A	25@V <sub>GS</sub> = 4.5 V 40@V <sub>GS</sub> = 2.5 V

### FEATURES

- Super high dense cell design for low R<sub>DS(ON)</sub>.
- Rugged and reliable.
- Surface Mount Package.



### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25 °C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	20	V
Gate-Source Voltage	V <sub>GS</sub>	±12	V
Drain Current-Continuous @ T <sub>J</sub> =25 °C -Pulsed <sup>b</sup>	I <sub>D</sub>	5	A
	I <sub>DM</sub>	25	A
Drain-Source Diode Forward Current <sup>a</sup>	I <sub>S</sub>	2	A
Maximum Power Dissipation <sup>a</sup>	P <sub>D</sub>	1.25	W
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

### THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient <sup>a</sup>	R <sub>θJA</sub>	100	°C/W
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